Product data sheet

Product profile

1.1 General description

Dual small-signal P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Trench MOSFET technology
- 2 kV ElectroStatic Discharge (ESD) protection

1.3 Applications

- Relay driver
- High-speed line driver

- High-side load switch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	<u>[1]</u>	-	-	-4.2	Α
Static charact	eristics (per transistor)						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2 \text{ A}; T_j = 25 \text{ °C}$		-	66	79	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D4 D0
2	G1	gate TR1	6 5 4	D1 D2
3	D2	drain TR2		
4	S2	source TR2		G1 $G2$
5	G2	gate TR2		
6	D1	drain TR1	1 2 3	
7	D1	drain TR1	Transparent top view	S1 S2 017aaa260
8	D2	drain TR2	DFN2020-6 (SOT1118)	

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMDPB70XPE	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1118		

4. Marking

Table 4. Marking codes

Type number	Marking code
PMDPB70XPE	2B

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	tor					
V_{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	<u>[1]</u>	-	-4.2	Α
		V _{GS} = -4.5 V; T _{amb} = 25 °C	<u>[1]</u>	-	-3	Α
		$V_{GS} = -4.5 \text{ V}; T_{amb} = 100 \text{ °C}$	<u>[1]</u>	-	-2.1	Α
I _{DM}	peak drain current	$T_{amb} = 25 ^{\circ}C$; single pulse; $t_p \le 10 \mu s$		-	-12	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	515	mW
				-	1210	mW
		T _{sp} = 25 °C		-	8330	mW
Source-dra	in diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.3	Α
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Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

		<u> </u>				
Symbol	Parameter	Conditions		Min	Max	Unit
ESD maximum	n rating					
V_{ESD}	electrostatic discharge voltage	HBM; C = 100 pF; R = 1.5 kΩ	[3]	-	2000	V
Per device						
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

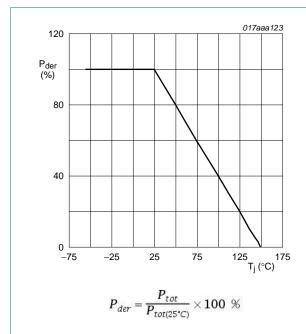


Fig 1. Normalized total power dissipation as a function of junction temperature

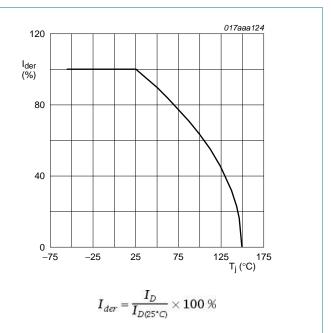


Fig 2. Normalized continuous drain current as a function of junction temperature

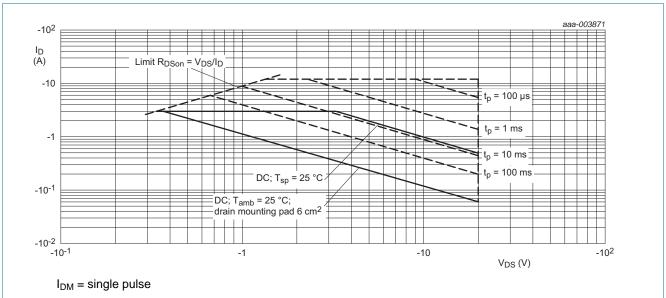


Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
R _{th(j-a)} thermal resistance		in free air	<u>[1]</u>	-	212	244	K/W
	from junction to ambient		[2]	-	90	104	K/W
	ambient	in free air; t ≤ 5 s	[2]	-	55	64	K/W
$R_{th(j\text{-sp})}$	thermal resistance from junction to solder point			-	11	15	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

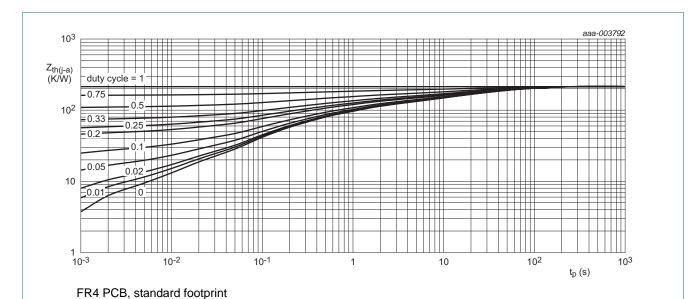
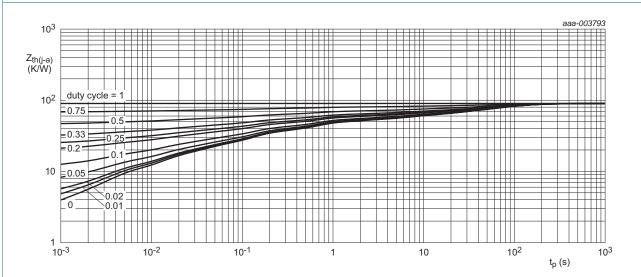


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

5 of 15

7. Characteristics

Table 7. Characteristics

Table 1.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics (per transistor)					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.75	-1	-1.25	V
I _{DSS} c	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	10	μΑ
		$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
R _{DSon}	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -2 \text{ A}; T_j = 25 \text{ °C}$	-	66	79	mΩ
resistance	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2 \text{ A}; T_j = 150 \text{ °C}$	-	94	112	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -1.5 \text{ A}; T_j = 25 \text{ °C}$	-	98	123	mΩ
9 _{fs}	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -2 \text{ A}; T_j = 25 \text{ °C}$	-	7.3	-	S
Dynamic	characteristics (per transist	or)				
Q _{G(tot)}	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -2 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	5	7.5	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	1.1	-	nC
Q_{GD}	gate-drain charge		-	1.1	-	nC
C _{iss}	input capacitance	$V_{DS} = -10 \text{ V; } f = 1 \text{ MHz; } V_{GS} = 0 \text{ V;}$	-	600	-	pF
Coss	output capacitance	T _j = 25 °C	-	103	-	pF
C _{rss}	reverse transfer capacitance		-	77	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = -10 \text{ V}; I_D = -2 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	16	-	ns
t _{d(off)}	turn-off delay time		-	33	-	ns
t _f	fall time		-	15	-	ns
Source-di	rain diode (per transistor)					
V_{SD}	source-drain voltage	$I_S = -0.5 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_i = 25 \text{ °C}$	-	-0.7	-1.2	V

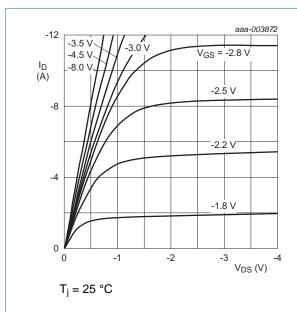


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

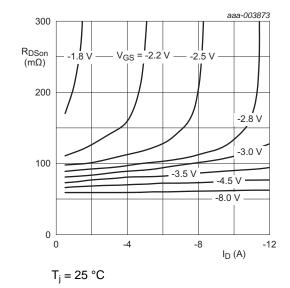
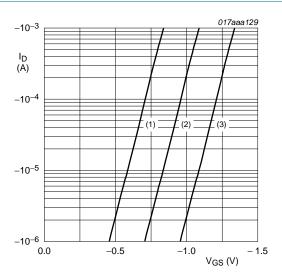


Fig 8. Drain-source on-state resistance as a function of drain current; typical values



 $T_j = 25 \, ^{\circ}C; \, V_{DS} = -3 \, V$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage

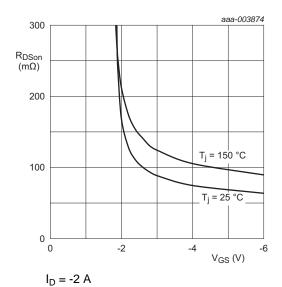


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

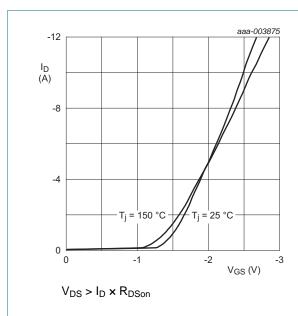


Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

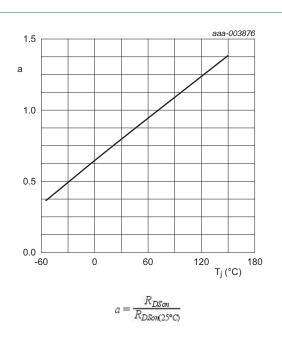


Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

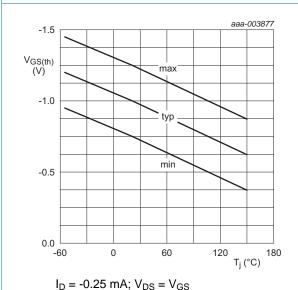
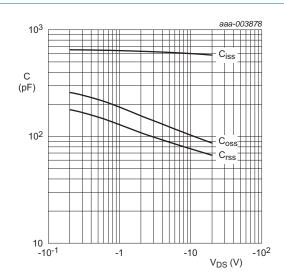


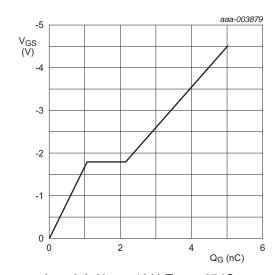
Fig 12. Gate-source threshold voltage as a function of

junction temperature



 $f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 I_D = -2 A; V_{DS} = -10 V; T_{amb} = 25 °C

Fig 14. Gate-source voltage as a function of gate charge; typical values

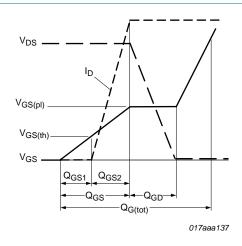
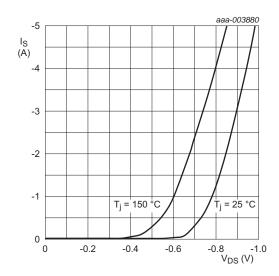


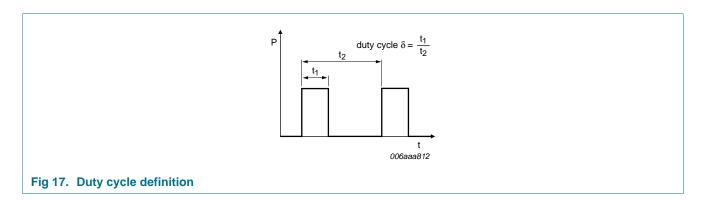
Fig 15. Gate charge waveform definitions



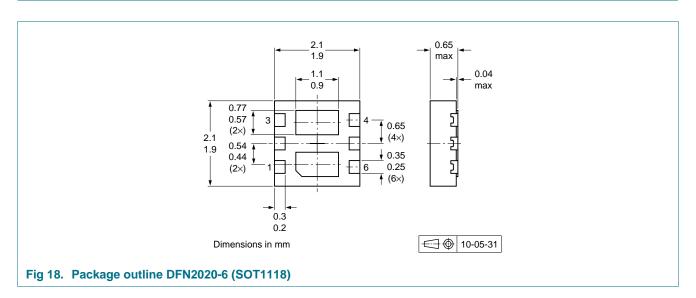
 $V_{GS} = 0 V$

Fig 16. Source current as a function of source-drain voltage; typical values

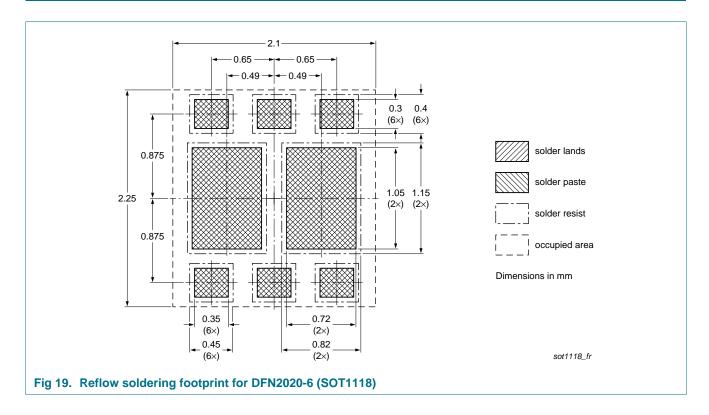
8. Test information



9. Package outline



10. Soldering





11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMDPB70XPE v.1	20120620	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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14 of 15

PMDPB70XPE

20 V dual P-channel Trench MOSFET

14. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Marking2
5	Limiting values2
6	Thermal characteristics4
7	Characteristics6
8	Test information10
9	Package outline
10	Soldering11
11	Revision history12
12	Legal information13
12.1	Data sheet status
12.2	Definitions13
12.3	Disclaimers
12.4	Trademarks14
13	Contact information

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